

*CLAIM AMENDMENTS*

1 and 2 (Cancelled)

3. (Currently Amended) A method of manufacturing a semiconductor device comprising ~~the steps of:~~

using a lead frame ~~composed of~~ including a plate-like body having ~~an uneven~~ a non-planar upper surface and a plain planar under surface, ~~said plate-like body comprising~~ a first thin portion for mounting a semiconductor chip ~~provided with~~ and having a plurality of pad electrodes, a plurality of first thick portions ~~provided around~~ radially arranged in said first thin portion for forming lead electrodes respectively ~~arranged~~ corresponding to the pad electrodes of ~~said the~~ semiconductor chip, a second thin portion ~~provided~~ located between pairs of said plurality of first thick portions, a third thin portion ~~provided for~~ peripherally surrounding said plurality of first thick portions, and a second thick portion ~~provided around~~ surrounding said third thin portion;

sealing integrally ~~said the~~ semiconductor chip; and said lead electrodes ~~and~~ connecting means up to the same surface as ~~that of~~ all of said first, second, and third thin portions with a ~~seal resin layer~~, after making a connection between said plurality of pad electrodes of ~~said the~~ semiconductor chip mounted on said first thin portion and said plurality of lead electrodes ~~by said~~ with connecting means; and

removing said first, second, and third thin portions by etching so that each of said plurality of lead electrodes includes a thin internal lead portion having a connection part ~~to~~ to ~~said connecting means on the~~ an upper surface side and a thick external electrode portion protruding toward ~~the~~ an under surface and forming a connection part ~~to outside;~~, wherein said ~~seal resin layer is formed so that the~~ has an underside thereof forms substantially ~~the same surface~~ co-planar with as the under surface of the internal lead portion of said lead electrodes, and so that said external electrode portion protrudes ~~downward~~ outward from the underside of said ~~seal resin layer~~.

4. (Currently Amended) The method of manufacturing a semiconductor device according to claim 3, wherein the first, second, and third thin portions have substantially the same thickness.

5. (Currently Amended) A method of manufacturing a semiconductor device comprising ~~the steps of:~~

using a lead frame ~~composed of~~ including a plate-like body having ~~an uneven~~ a non-planar upper surface and a plain planar under surface, ~~said plate-like body comprising~~ a first thin portion for mounting a semiconductor chip ~~provided with~~ and having a plurality of pad electrodes, a plurality of first thick portions ~~provided around~~ radially arranged in said first thin portion for forming lead electrodes respectively ~~arranged~~ corresponding to the pad electrodes of ~~said the~~ semiconductor chip, a second thin portion ~~provided~~ located between pairs of said plurality of first thick portions, a third thin portion ~~provided for~~ peripherally surrounding said plurality of first thick portions, ~~and~~ a second thick portion ~~provided around~~ surrounding said third thin portion to form an auxiliary electrode, a fourth thin portion ~~provided around~~ surrounding said second thick portion, and a third thick portion ~~provided around~~ surrounding said fourth thin portion;

sealing integrally ~~said the~~ semiconductor chip, said lead electrodes, ~~connecting means~~ and said auxiliary electrode ~~up~~ to the same surface as ~~that of~~ all of said first, second, third, and fourth thin portions with a ~~seal resin layer~~, after making a connection between said plurality of pad electrodes of said semiconductor chip mounted on said first thin portion and said plurality of lead electrodes ~~by said~~ with connecting means and making a connection between said lead electrodes and said auxiliary electrode; and

removing said first, second, third and fourth thin portions by etching so that each of said plurality of lead electrodes includes a thin internal lead portion having a connection part ~~to said connecting means on the~~ an upper surface side and a thick external electrode portion protruding toward ~~the~~ an under surface and forming a connection part ~~to outside,~~ wherein said ~~seal resin layer is formed so that the~~ has an underside thereof forms substantially ~~the same surface as~~ co-planar with the under surface of the internal lead portion of said lead electrodes and said auxiliary electrode, and so that said external electrode portion protrudes ~~downward~~ outward from the underside of said ~~seal resin layer~~.

6. (Currently Amended) The method of manufacturing a semiconductor device according to claim 5, wherein the first, second, third, and fourth thin portions have substantially the same thickness.